## MSKSEMI















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# Broduct data sheet



### FMMT449 TRANSISTOR (NPN)



**SOT - 23** 



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

#### **FEATURES**

Low Equivalent On-Resistance

MARKING: 449

MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current	1	Α
Pc	Collector Power Dissipation	200	mW
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
Tj	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~+150	$^{\circ}$

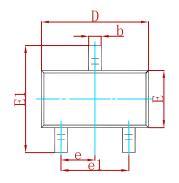
**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)** 

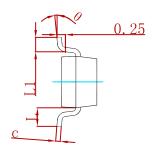
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =1mA, I <sub>E</sub> =0	50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB}$ =4 $V$ , $I_{C}$ =0			0.1	μA
	h <sub>FE(1)</sub> *	V <sub>CE</sub> =2V, I <sub>C</sub> =50mA	70			
DC current gain	h <sub>FE(2)</sub> *	V <sub>CE</sub> =2V, I <sub>C</sub> =500mA	100		300	
Do current gam	h <sub>FE(3)</sub> *	V <sub>CE</sub> =2V, I <sub>C</sub> =1A	80			
	h <sub>FE(4)</sub> *	V <sub>CE</sub> =2V, I <sub>C</sub> =2A	40			
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub> *	I <sub>C</sub> =1A, I <sub>B</sub> =100mA			0.5	V
Conector-entitler saturation voitage	V <sub>CE(sat)2</sub> *	I <sub>C</sub> =2A, I <sub>B</sub> =200mA			1	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub> *	I <sub>C</sub> =1A, I <sub>B</sub> =100mA			1.25	V
Base-emitter voltage	V <sub>BE</sub> *	V <sub>CE</sub> =2V, I <sub>C</sub> =1A			1	V
Transition fraguency	f_	V <sub>CE</sub> =10V,I <sub>C</sub> =50mA,	150		Ŋ	MHz
Transition frequency	f⊤	f=100MHz				IVITZ
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			15	pF

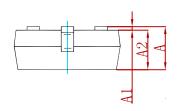
<sup>\*</sup>Pulse test



#### **PACKAGE MECHANICAL DATA**

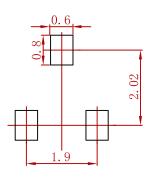






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Зупівої	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
Ĺ	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

#### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
FMMT449	SOT-23	3000



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